

L Number	Hit	Search Text	DB	Time stamp
245	21	(pad sam (parasiti n ar5 (s r or r tifier)) and ((rectifi r or scr) near10 (l w near v ltag )))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:07
246	0	(pad same (parasitic near5 (scr or rectifier)) and ((rectifier or scr) near10 (low near voltage))).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:07
247	3	(pad same (parasitic near5 (scr or rectifier)) and ((rectifier or scr) near10 (low near voltage))).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:08
248	5	(pad near10 (parasitic near5 (scr or rectifier)) and ((rectifier or scr) near10 (low near voltage)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:09
249	2	(pad near10 (parasitic near5 (scr or rectifier)) and ((rectifier or scr) near10 (low near voltage))) and pad.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:09
250	2	(pad near10 (parasitic near5 (scr or rectifier)) and ((rectifier or scr) near10 (low near voltage))) and pad.clm. and diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:09
251	0	(pad near10 (parasitic near5 (scr or rectifier)) and ((rectifier or scr) near10 (low near voltage))) and pad.clm. and diode.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:09
252	158	diode.clm. and (mosfet or mos or transistor).clm. and pad.clm. and esd.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:09
253	32	diode.clm. and (mosfet or mos or transistor).clm. and pad.clm. and esd.clm. and (scr or rectifier).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:10
254	4	di d . lm. and (m sf t r mos r transistor). lm. and pad. lm. and sd.clm. and (s r or r tifi r).clm. and (l w near v ltag ).clm.	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:10

255	1	diode.clm. and (m sf t r mos or transist r). lm. and pad.clm. and esd.clm. and (s r r rectifi r).clm. and (l w n ar v ltage).clm. and (pad n ar10 di de near10 (mos or mosfet or transistor)). lm.	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:18
256	94	(di de near10 (transistor r m sf t or m s) near10 pad).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:19
257	5	(diode near10 (transistor or mosfet or mos) near10 pad).clm. and (scr or rectifier).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:20
258	3	(diode near10 (transistor or mosfet or mos) near10 pad).clm. and (scr or rectifier).clm. and ((rectifier or scr) near10 esd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:20
259	1	(diode near10 (transistor or mosfet or mos) near10 pad).clm. and (scr or rectifier).clm. and ((rectifier or scr) near10 (esd near current))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:22
260	1	(diode near10 (transistor or mosfet or mos) near10 pad).clm. and (scr or rectifier).clm. and ((rectifier or scr or lvscr) near10 (esd near current))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:22
261	116	((rectifier or scr or lvscr) near10 (esd near current))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:22
262	2	((rectifier or scr or lvscr) near10 (esd near current)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:23
263	2	((rectifier or scr or lvscr) near10 (esd near current) near10 (lvscr or (low near voltage)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:24
264	730	((rectifier or scr or lvscr) near10 (current) near10 (lvscr or (low near voltage)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:24

265	14	( sd near10 (rectifi r or scr or lvscr) near10 ( urr nt) n ar10 (lvscr or (l w near v ltage)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:25
266	1	(esd n ar10 (rectifier r cr r lvscr) n ar10 (current) near10 (lvscr or (low near voltage)) near10 (distribute or distributing or distributed or distribution or pass or passed))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:26
267	5	((lvscr or (low near current)) near10 diode near10 esd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:27
268	0	((lvscr)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:28
269	14	((lvscr))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:28
270	0	((lvscr)) and pad.clm. and diode.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:28
271	11	((lvscr)) and pad and diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:29
272	2	((lvscr)) and (pad same diode same (transistor or mosfet or mos))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:30
273	2	(diode near10 (transistor or mosfet or mos) near10 pad near10 (rectifier or scr or lsvscr) near10 esd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:34
274	0	(diode near10 (transistor or mosfet or mos) near10 pad near10 (rectifier or scr or lsvs r) near10 sd near10 (l w n ar2 voltage))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:34

275	0	(diode near10 (transistor or mosfet or mos) near10 pad near10 (rectifier or scr or lvscr) near10 esd near10 (low near2 voltage))	USPAT; US-P PUB; EPO; JP ; DERWENT; IBM_TDB	2004/06/08 16:35
276	2	((diode near10 (transistor or mosfet or mos) near10 pad near10 (rectifier or scr or lvscr) near10 esd) same (low near2 voltage))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:38
277	13	((diode near10 (transistor or mosfet or mos) near10 (rectifier or scr or lvscr) near10 esd) same (low near2 voltage))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:38
278	2	((diode near10 (transistor or mosfet or mos) near10 (rectifier or scr or lvscr) near10 esd) same (low near2 voltage) same (esd near current))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:38
279	3	((diode near10 (transistor or mosfet or mos) near10 (rectifier or scr or lvscr)) same (low near2 voltage) same (esd near current))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:41
280	6	((diode near20 (transistor or mosfet or mos) near20 (rectifier or scr or lvscr)) same (low near2 voltage) same (esd near current))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:42
281	31	((rectifier or scr or lvscr) near10 (low near2 voltage) same (esd near current))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:42
282	5	((rectifier or scr or lvscr) near10 (low near2 voltage) near10 (esd near current))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:44
283	7	((rectifier or scr or lvscr) near20 (low near2 voltage) near20 (esd near current))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:44
284	1190	((rectifier or scr or lvscr) near20 (low near2 voltage) near20 (current))	USPAT; US-PGPUB; EPO; JP ; DERWENT; IBM_TDB	2004/06/08 16:45

285	8	((rectifier or scr or lvscr) near20 (low near2 voltage) near20 (current)).ti,ab,clm. and esd.ti,ab,clm.	USPAT; US-PGPUB; EP ; JPO; DERWENT; IBM_TDB	2004/06/08 16:45
286	3	((rectifier or scr or lvscr) near20 (low near2 voltage) near20 (current)).ti,ab,clm. and esd.ti,ab,clm. and parasitic.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:45
287	1	((rectifier or scr or lvscr) near20 (low near2 voltage) near20 (current)).ti,ab,clm. and esd.ti,ab,clm. and parasitic.ti,ab,clm. and diode.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:47
288	1	((rectifier or scr or lvscr) near20 (low near2 voltage) near20 (current)).ti,ab,clm. and esd.ti,ab,clm. and parasitic.ti,ab,clm. and (diode near10 transistor).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:47
289	94	(diode near10 (mos or mosfet or transistor) near10 pad).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:48
290	26	(diode near10 (mos or mosfet or transistor) near10 pad).clm. and esd.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:48
291	3	(diode near10 (mos or mosfet or transistor) near10 pad).clm. and esd.clm. and (rectifier or scr or lvscr).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:50
292	1	(diode near10 (mos or mosfet or transistor) near10 pad).clm. and esd.clm. and (rectifier or scr or lvscr).clm. and (low near2 voltage).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:51
293	2	(diode near10 (mos or mosfet or transistor) near10 pad).clm. and esd.clm. and (rectifier or scr or lvscr).clm. and (low near2 voltage).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:52
294	42	(low near2 voltage) near10 (esd near current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:53

295	15	((I w near2 v ltag ) n ar10 ( sd n ar current)) and di d .ti,ab,clm. and (m sf t r m s or transist r).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:53
296	13	((I w near2 voltag ) near10 ( sd near current)) and diode.ti,ab,clm. and (mosfet or mos or transistor).ti,ab,clm. and parasitic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:54
297	6	((low near2 voltage) near10 (esd near current)) and diode.ti,ab,clm. and (mosfet or mos or transistor).ti,ab,clm. and parasitic and pad.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:54
298	4	((low near2 voltage) near10 (esd near current)) and diode.ti,ab,clm. and (mosfet or mos or transistor).ti,ab,clm. and parasitic and pad.clm. and (rectifier or scr or lvscr).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:55
299	2	((low near2 voltage) near10 (esd near current)) and diode.ti,ab,clm. and (mosfet or mos or transistor).ti,ab,clm. and parasitic.clm. and pad.clm. and (rectifier or scr or lvscr).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:57
300	0	((low near2 voltage) near10 (esd near current)).clm. and diode.ti,ab,clm. and (mosfet or mos or transistor).ti,ab,clm. and parasitic.clm. and pad.clm. and (rectifier or scr or lvscr).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:57
301	0	((low near2 voltage) same (esd near current)).clm. and diode.ti,ab,clm. and (mosfet or mos or transistor).ti,ab,clm. and parasitic.clm. and pad.clm. and (rectifier or scr or lvscr).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:58
302	3	(diode same (mos or mosfet or transistor) same parasitic same (rectifier or scr or lvscr) same (esd near current) same (low near2 voltage))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:59
303	2	(diode same (mos or mosfet or transistor) same parasitic same (rectifier or scr or lvscr) same (esd near current) same (low near2 voltage) same pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 16:59